



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

1SS355

## SOD-323 Switching Diode 开关二极管

### ■ Features 特点

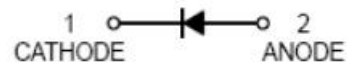
Fast Switching Speed 快的开关速度

Surface mount device 表面贴装器件

High Conductance 高电导率

Case 封装:SOD-323

Marking 印字: A



### ■ Maximum Rating 最大额定值

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

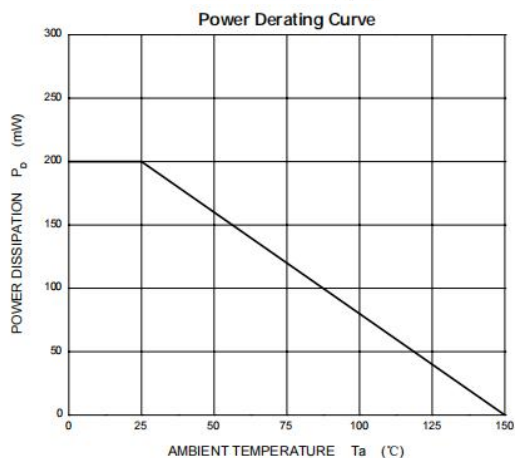
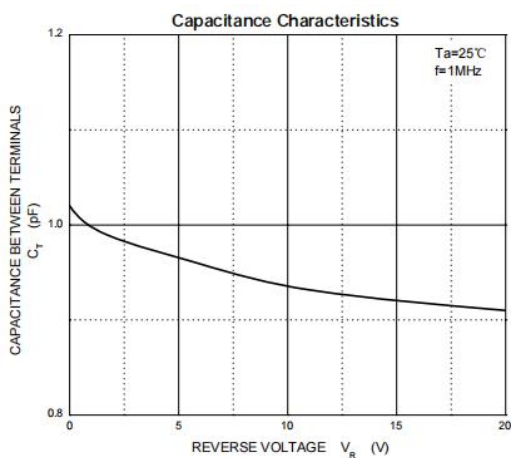
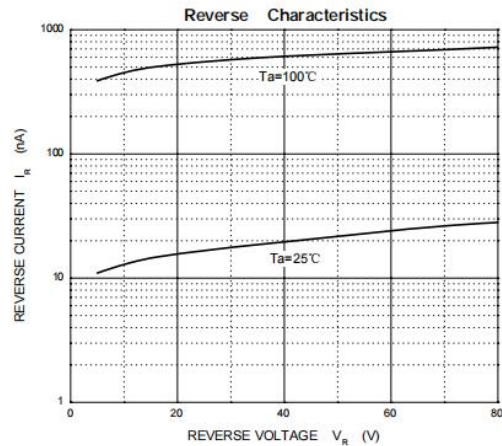
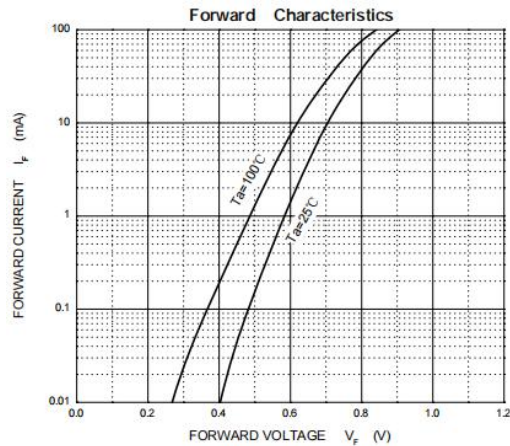
Characteristic 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Non-Repetitive Peak Reverse Voltage 不重复反向峰值电压	$V_{RM}$	90	V
DC Reverse Voltage 直流反向电压	$V_R$	80	V
Forward Rectified Output Current 正向工作电流	$I_O$	100	mA
Non-Repetitive Peak Surge Current 不重复峰值浪涌电流	$I_{FSM}$	225	mA
Power Dissipation 耗散功率	$P_D$	200	mW
Thermal Resistance Junction-Ambient 结到环境热阻	$R_{\theta JA}$	625	$^{\circ}\text{C}/\text{W}$
Junction/Storage Temperature 结温/储藏温度	$T_J, T_{stg}$	-50to+150 $^{\circ}\text{C}$	$^{\circ}\text{C}$

### ■ Electrical Characteristics 电特性

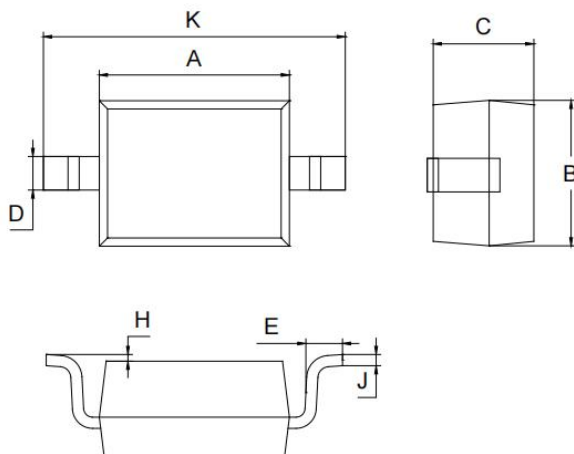
( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位	Condition 条件
Reverse Voltage 反向电压	$V_R$	80		V	$I_R=1\mu\text{A}$
Forward Voltage 正向电压	$V_F$		1.2	V	$I_F=100\text{mA}$
Reverse Current 反向电流	$I_R$		0.1	$\mu\text{A}$	$V_R=80\text{V}$
Recovery Time 反向恢复时间	$T_{rr}$		4	nS	$V_R=6\text{V}$
Junction Capacitance 结电容	$C_J$		3	pF	$V_R=0.5\text{V}$

## Typical Characteristic Curve 典型特性曲线



## Dimension 外形封装尺寸



SOD-323		
Dim	Min	Max
A	1.60	1.80
B	1.20	1.40
C	0.80	0.90
D	0.25	0.35
E	0.22	0.42
H	0.02	0.10
J	0.05	0.15
K	2.55	2.75
All Dimensions in mm		